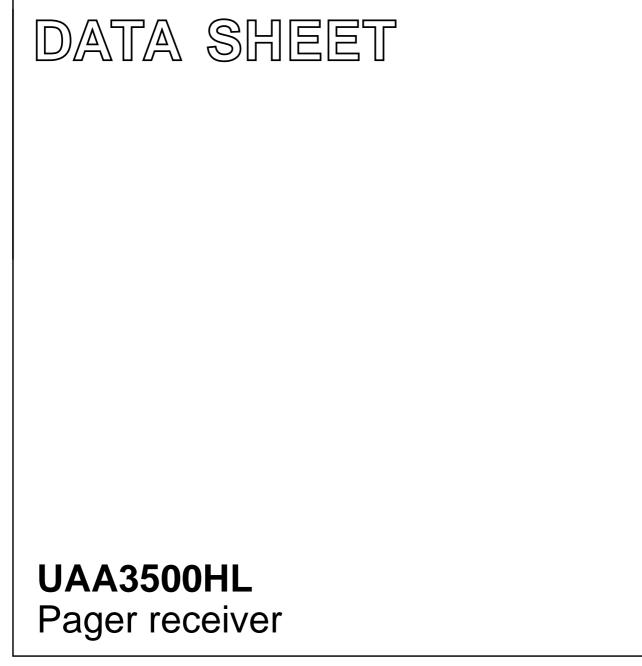
# INTEGRATED CIRCUITS



Objective specification File under Integrated Circuits, IC17 1999 Mar 30



HILIPS

# **UAA3500HL**

### FEATURES

- Double frequency conversion, zero-IF receiver with:
  Configurable in all paging bands (130 to 930 MHz)
  - Low noise amplifier featured with four step Automatic Gain Control (AGC)
  - Down-conversion mixers
  - On-chip, zero-IF channel filter
  - I/Q, non-demodulated outputs
  - Highpass filters to remove DC offsets.
- External Voltage Controlled Oscillator (VCO).
  - Both LOs derived from the VCO.

### **APPLICATIONS**

- FLEX, ERMES and POCSAG pagers
- Remote control terminals.

### **GENERAL DESCRIPTION**

The UAA3500HL is a one-chip pager receiver complying with POCSAG, FLEX and ERMES standards. The IC performs in accordance with specifications in the -10 to +55 °C temperature range.

The UAA3500HL contains a front-end receiver configurable, through external components, for any frequency band between 130 and 930 MHz. The back-end receiver consists of the channel filter and limiters. An external VCO ensures the Local Oscillator (LO) for the front-end. Designed in an advanced BiCMOS process, it combines high performance with low-power consumption and a high degree of integration, thus reducing external component costs and total radio size.

Its first advantage is to remove the expensive SAW filter necessary in a superhet architecture and to replace it by an integrated, elliptic channel filter that provides 70 dB adjacent channel rejection. The receive front-end section consists of a low-noise amplifier that drives mixers through an external LC image rejection filter. The output drives the I and Q second mixers, whose outputs are at zero frequency. The receiver back-end section consists of filters (channel filtering), limiters (limited output required) and high-pass filters (DC-block) to remove DC offsets. Outputs are I and Q, undemodulated signals.

Its second advantage is to provide the two LO signals only from one VCO tuned by a PLL. On-chip frequency divider-by-2 and buffers provide the LO sources.

Its third advantage is to provide two voltage regulators, allowing to obtain 1.0 and 1.8 V regulated voltages.

### ORDERING INFORMATION

TYPE NUMBER		PACKAGE				
	NAME DESCRIPTION		VERSION			
UAA3500HL	LQFP48	plastic low profile quad flat package; 48 leads; body $7 \times 7 \times 1.4$ mm	SOT313-2			

# UAA3500HL

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS <sup>(1)</sup>	MIN.	TYP.	MAX.	UNIT
V <sub>CC1</sub>	supply voltage 1 (B++)		1.85	2.1	3.3	V
V <sub>CC2</sub>	supply voltage 2 (B+)		1.05	1.4	1.5	V
I <sub>CC1(RX)</sub>	receive supply current from B++	160 MHz	-	2.4	-	mA
		280 MHz	-	2.4	-	mA
		930 MHz	_	2.5	-	mA
I <sub>CC2(RX)</sub>	receive supply current from B+	160 MHz	-	1.3	-	mA
		280 MHz	_	1.4	-	mA
		930 MHz	_	2.3	-	mA
NF <sub>RX</sub>	receiver noise figure	160 MHz	_	2.7	-	dB
		280 MHz	_	3.1	-	dB
		930 MHz	_	4.4	-	dB
Sens	sensitivity; 3% BER and 1600 bits/s	160 MHz	_	-128.5	-	dBm
	2 level	280 MHz	_	-128	-	dBm
		930 MHz; note 2	_	-126.5	-	dBm
ACR	adjacent channel rejection		65	70	-	dB
T <sub>amb</sub>	operating ambient temperature		-10	+25	+55	°C

### Notes

1. For 930 MHz band; for other conditions see Chapters "DC characteristics" and "AC characteristics".

2. Sensitivity; 3% BER and 6400 bits/s 4 level: -123 dBm.

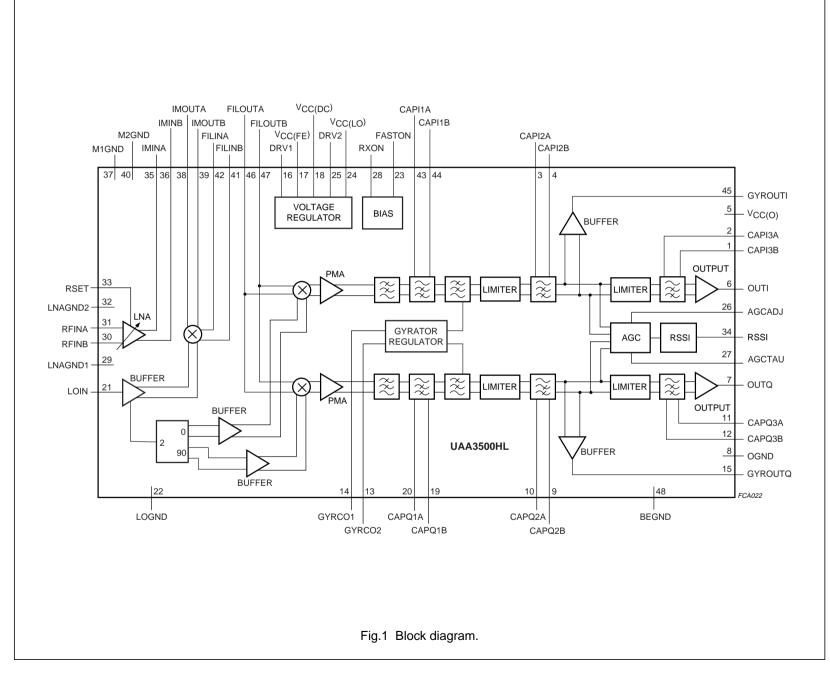
Philips Semiconductors

# Objective specification

# Pager receiver

# **UAA3500HL**





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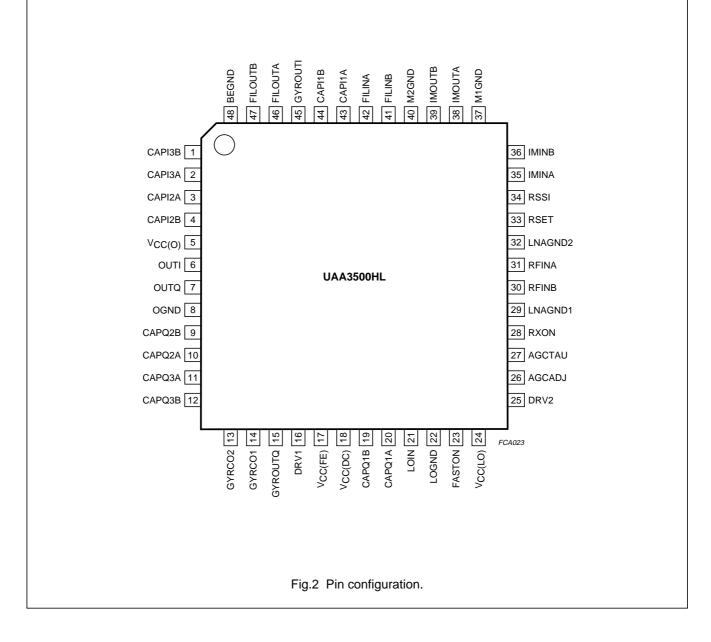
# UAA3500HL

### PINNING

SYMBOL	PIN	DESCRIPTION
CAPI3B	1	3rd DC filter (I path) external capacitor B (I path)
CAPI3A	2	3rd DC filter (I path) external capacitor A (I path)
CAPI2A	3	2nd DC filter (I path) external capacitor A (I path)
CAPI2B	4	2nd DC filter (I path) external capacitor A (I path)
V <sub>CC(O)</sub>	5	output stage supply voltage B (I path)
OUTI	6	output I and Q signals (I path)
OUTQ	7	output I and Q signals (Q path)
OGND	8	output stage ground
CAPQ2B	9	2nd DC filter external capacitor B (Q path)
CAPQ2A	10	2nd DC filter external capacitor A (Q path)
CAPQ3A	11	3rd DC filter external capacitor A (Q path)
CAPQ3B	12	3rd DC filter external capacitor B (Q path)
GYRCO2	13	external resistor to set-up gyrator filter cut-off frequency
GYRCO1	14	external resistor to set-up gyrator filter cut-off frequency
GYROUTQ	15	Q-gyrator output
DRV1	16	regulator driver (1.8 V)
V <sub>CC(FE)</sub>	17	regulated voltage for front-end (1.8 V)
V <sub>CC(DC)</sub>	18	input voltage from DC-to-DC converter (2.1 V)
CAPQ1B	19	1st DC filter external capacitor (Q path)
CAPQ1A	20	1st DC filter external capacitor (Q path)
LOIN	21	LO input
LOGND	22	LO strip ground
FASTON	23	fast mode enable
V <sub>CC(LO)</sub>	24	regulated voltage for LO strip (1.0 V)
DRV2	25	regulator driver (1.0)
AGCADJ	26	AGC loop gain control
AGCTAU	27	AGC loop time constant
RXON	28	receiver mode enable
LNAGND1	29	receiver LNA ground 1
RFINB	30	LNA input B
RFINA	31	LNA input A
LNAGND2	32	receiver LNA ground 2
RSET	33	LNA current setup
RSSI	34	received signal strength indicator
IMINA	35	image rejection filter input A
IMINB	36	image rejection filter input B
M1GND	37	first mixer ground
IMOUTA	38	image rejection filter output A
IMOUTB	39	image rejection filter output B
M2GND	40	second mixers ground

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SYMBOL	PIN	DESCRIPTION
FILINB	41	band filter input B
FILINA	42	band filter input A
CAPI1A	43	1st DC filter external capacitor (I path)
CAPI1B	44	1st DC filter external capacitor (I path)
GYROUTI	45	I-gyrator output
FILOUTA	46	band filter output to second mixers
FILOUTB	47	band filter output to second mixers
BEGND	48	receiver back-end ground



# UAA3500HL

### FUNCTIONAL DESCRIPTION

### **Receiver front-end section**

The receiver front-end consists of an LNA, followed by the first and the second mixers. For operation at low frequency (160 and 280 MHz for instance), the first mixer can be bypassed saving some current. The image rejection is made by an external LC filter placed between the LNA, the first mixer and the antenna selectivity. The IF band filtering is made by an external filter placed between the first mixer and the second ones. There are two second mixers for the two paths I and Q. The RF signals are in phase, and the LO signals are 90° shifted. The output signals are at zero frequency.

To increase the immunity to interferers an AGC loop controls the LNA gain by attenuating the RF input signal. Four steps of attenuation are possible (each having 8 dB), ranging therefore from 0 to 32 dB. The AGC loop threshold level and time constant may be controlled externally at pins AGCADJ and AGCTAU. The 2nd LO I/Q phase shift is made by a quadrature divider, whose input is the VCO oscillating signal.

The LNA current is setup by an external resistor. All the receivers (front-end and back-end) are turned on by the pin RXON.

### **Receiver back-end section**

The down-converted signal is amplified and then filtered by a Sallen-Key filter, that shows a notch at 15 kHz and about 6 dB rejection out-of-band. Then comes the first high-pass filter (DC-block), followed by the gyrator filter. It performs an elliptic, 7 poles low-pass filtering. The signal is then amplified by the first limiter, then filtered by the second DC-block, again amplified, and again filtered by the third DC-block. Finally an output stage delivers the signal with rail-to-rail logic levels. The first, second and third DC-block frequency are set at 4, 8 and 12 Hz respectively by external 330 nF capacitors.

The two voltage regulators are also activated by RXON.

At the output of the gyrator filter the signal is buffered and logarithmically converted. It controls then the AGC loop.

To rapidly reach the DC operating point a fast mode is built in the 3 DC-blocks.

LO

The external VCO is AC-coupled at input LOIN. It is then buffered to drive the first mixer. LOIN also enters a quadrature divider-by-2, whose output signals are also buffered to drive the second mixers. The VCO frequency should be  $\frac{2}{3}$  of that of the input RF signal.

The VCO synthesizer is integrated in the baseband controller chip, but an external synthesizer can also be used.

### **OPERATING MODES**

To use the IC, all V<sub>CC</sub> pins must be connected to the supply voltage B++ (2.1 V). The 1.8 V regulated voltage sinks current from B++ and the 1.0 V regulated voltage from B+ (1.4 V). In a typical application, the B+ supply is the battery and the B++ supply is the DC/DC converter located in the baseband chip.

In normal operating mode the receiver should be powered-on in fast mode. The fast mode can be turned off after several milliseconds.

Table 1 gives the definition of the polarity of the switching signals on the receive section.

SIGNAL	SECTION	LEVEL	ON/OFF
RXON	receive section powered-on	HIGH	on
	receive section powered-off	LOW	off
FASTON	fast mode powered-on	HIGH	on
	fast mode powered-off	LOW	off

Table 1	Switching signals on the receiver
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# UAA3500HL

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		-	6	V
∆GND	difference in ground supply voltage applied between all grounds	note 1	_	0.3	V
P <sub>I(max)</sub>	maximum power input		-	20	dBm
T <sub>j(max)</sub>	maximum operating junction temperature		-	150	°C
P <sub>(max)</sub>	maximum power dissipation	in stagnant air at 25 °C	-	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C

### Note

1. Pins short-circuited internally must be short-circuited externally.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	90	K/W

### HANDLING

Every pin withstands the ESD test in accordance with "MIL-STD-883C class 2 (method 3015.5)".

### **DC CHARACTERISTICS**

V<sub>CC</sub> = 2.1 V; T<sub>amb</sub> = 25 °C; 930 MHz band application, 3% BER and 1600 bits/s 2 level; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Pins: V <sub>CC(0</sub>	<sub>o)</sub> , 2 V1, 1 V0, 1 V0DRV, 1 V8, a	and 1 V8DRV	•	•		
V <sub>CC1</sub>	supply voltage 1 (B++)	over full temperature range	1.85	2.1	3.3	V
V <sub>CC2</sub>	supply voltage 2 (B+)	over full temperature range	1.05	1.4	1.5	V
I <sub>CC1(RX)</sub>	supply current from B++	RX section on; DC tested				
		160 MHz	-	2.4	-	mA
		280 MHz	_	2.4	_	mA
		930 MHz	_	2.5	_	mA
I <sub>CC2(RX)</sub>	supply current from B+	RX section on; DC tested				
		160 MHz	_	1.3	_	mA
		280 MHz	_	1.4	_	mA
		930 MHz	-	2.3	-	mA
I <sub>CC1(pd)</sub>	standby current from B++	Power-down mode; DC tested	0	0.5	1	μA
I <sub>CC2(pd)</sub>	standby current from B+	Power-down mode; DC tested	0	0.1	0.5	μA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Pins: RXO	N, FASTON, OUTI and OUTQ				1	-
VIH	HIGH-level voltage		V <sub>CC</sub> - 0.3	V <sub>CC</sub>	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	LOW-level voltage		-0.3	_	+0.4	V
I <sub>IH</sub>	HIGH-level static current	V <sub>CC</sub> – 0.4 V	-1	-	+1	μA
I <sub>IL</sub>	LOW-level static current	pin at 0.4 V	-1	-	+1	μA
Pins: CAPI	1A, CAPI1B, CAPQ1A and CA	APQ1B				
V <sub>CAP</sub>	DC level	RX section on	-	1.40	_	V
Pins: CAPI	2A, CAPI2B, CAPQ2A, CAPQ	2В, САРІЗА, САРІЗВ, САР	Q3A and CAF	Q3B		
V <sub>CAP</sub>	DC level	RX section on	-	1.57	_	V
Pins: RFIN	A and RFINB			•	•	•
V <sub>RF</sub>	DC level	RX section on	-	0.92	_	V
Pins: IMOL	JTA and IMOUTB		·			
VIMOUT	DC level	RX section on	-	0.17	_	V
Pins: FILIN	IA and FILINB			•	•	
V <sub>FILIN</sub>	DC level	RX section on	-	1	_	V
Pins: FILO	UTA and FILOUTB			•	•	-
V <sub>FILOUT</sub>	DC level	RX section on	-	0.24	-	V
Pins: GYR	OUTI and GYROUTQ	·		•	•	
V <sub>GYROUT</sub>	DC level	RX section on	-	1.42	_	V
Output sta	ge					
V <sub>OH</sub>	HIGH-level output voltage	I <sub>o</sub> = -5 μA	-	$V_{CC} - 0.2$	_	V
V <sub>OL</sub>	LOW-level output voltage	I <sub>o</sub> = 5 μA	_	0.2	_	V

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## AC CHARACTERISTICS

V<sub>CC</sub> = 2.1 V; T<sub>amb</sub> = 25 °C; 930 MHz band application, 3% BER and 1600 bits/s 2 level; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	
Receiver		1	1	1		1
G <sub>CP</sub>	front-end conversion power gain	from RF input to 2nd mixer input				
		160 MHz	_	20	_	dB
		280 MHz	_	12.8	_	dB
		930 MHz	_	12.7	-	dB
NF <sub>RX</sub>	receiver noise figure	from RF input to 2nd mixer input				
		160 MHz	_	2.7	-	dB
		280 MHz	_	3.1	_	dB
		930 MHz	_	4.4	-	dB
IP1	1 dB input compression point	from RF input to 2nd mixer input	_	-38	-	dBm
IP2	2nd order intercept point	from 2nd mixer input to gyrator output	45	-	-	dBm
IP3	3rd order intercept point	from RF input to 2nd mixer input; note 1	-	-33	-	dBm
CCR	co-channel rejection	threshold +3 dB	_	5	_	dB
ACR	adjacent channel rejection	channel spacing = 25 kHz; from RF input to gyrator output	65	70	-	dB
Blocking	blocking immunity	frequency offset >1 MHz	75	80	_	dB
G <sub>AGC</sub>	front-end gain reduction by AGC step		-	8	-	dB
AGC <sub>th</sub>	AGC threshold	above sensitivity	20	25	30	dB
t <sub>turnon</sub>	establishment time	until sensitivity +3 dB is reached	_	-	30	ms
ΔIQ	IQ channel unbalance		_	-	2	dB
R <sub>LNA</sub>	LNA current set resistor	160 MHz	_	56	-	kΩ
		280 MHz	-	47	-	kΩ
		930 MHz	_	27	-	kΩ
R <sub>gyr</sub>	gyrator cut-off frequency set resistor	cut-off frequency = 8 kHz	-	47	-	kΩ
LO						
f <sub>VCO</sub>	VCO frequency		_	²∕₃RF	_	Hz

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	
LNA	1			4	1	1
G <sub>LNA</sub>	RF amplifier power gain	from RF input to image filter output				
		160 MHz	_	20	_	dB
		280 MHz	_	16.2	_	dB
		930 MHz	_	14.9	_	dB
NF <sub>LNA</sub>	RF amplifier noise figure	from RF input to image filter output				
		160 MHz	_	1.8	-	dB
		280 MHz	_	1.9	-	dB
		930 MHz	_	2.2	_	dB
IP1 <sub>LNA</sub>	1 dB input compression point	from RF input to image filter output	-	-27	-	dBm
IP3 <sub>LNA</sub>	3rd order intercept point	from RF input to image filter output	-	-17.6	-	dBm
First mixer		·				
G <sub>FM</sub>	1st mixer power gain		_	2.2	-	dB
NF <sub>FM</sub>	1st mixer noise figure		_	10.2	_	dB
IP1 <sub>FM</sub>	1 dB input compression point		_	-22	_	dBm
IP3 <sub>FM</sub>	3rd order intercept point		_	-14	_	dBm
Second mi	xer + PMA + Sallen-Key + 1st D	C block + gyrator filter				•
G	power gain	from 2nd mixer input to gyrator output	-	10.4	-	dB
IM3	3rd order intermodulation	from 2nd mixer input to gyrator output	55	-	-	dB
1st DC blo	ck					
f <sub>cut-off</sub>	cut-off frequency	measured at gyrator output	_	4	_	Hz

Note

1. The two tones for intermodulation test would normally be set at 2 and 4 or 4 and 8 channels for type approval tests i.e 930 and 930.1 or 930.1 and 930.2 MHz.

# UAA3500HL

### **APPLICATION INFORMATION**

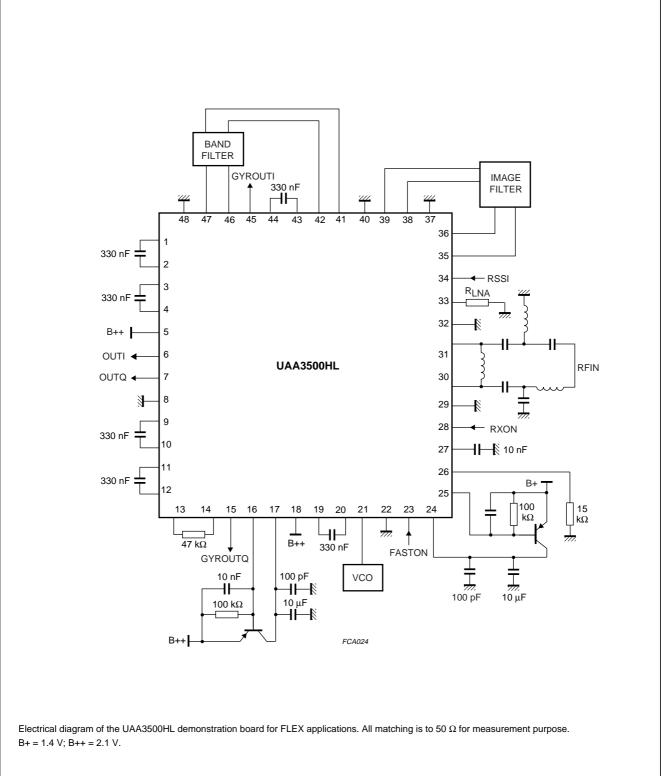
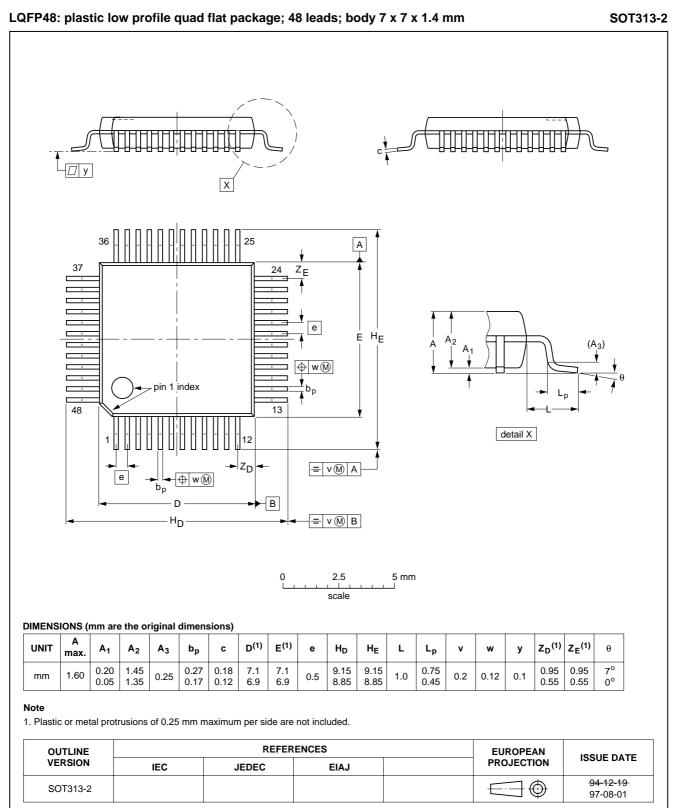


Fig.3 Demonstration board diagram.

# UAA3500HL

### PACKAGE OUTLINE



# UAA3500HL

### SOLDERING

### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

### **Reflow soldering**

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320  $^\circ\text{C}.$ 

# **UAA3500HL**

## Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW <sup>(1)</sup>
BGA, SQFP	not suitable	suitable
HLQFP, HSQFP, HSOP, HTSSOP, SMS	not suitable <sup>(2)</sup>	suitable
PLCC <sup>(3)</sup> , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended <sup>(3)(4)</sup>	suitable
SSOP, TSSOP, VSO	not recommended <sup>(5)</sup>	suitable

### Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

### DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

### LIFE SUPPORT APPLICATIONS

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